TOSHIBA Field-Effect Transistor Silicon N / P Channel MOS Type

SSM6L40TU

○ Power Management Switch Applications

- High-Speed Switching Applications
- N-ch: 4.0-V drive
- P-ch: 4.0 -V drive
- N-ch, P-ch, 2-in-1

Low ON-resistance Q1 N-ch: $R_{on} = 182 \text{ m}\Omega \text{ (max)} (@V_{GS} = 4 \text{ V})$

 R_{on} = 122 m Ω (max) (@V_{GS} = 10 V)

Q2 P-ch: R_{on} = 403 m Ω (max) (@V_{GS} = -4 V)

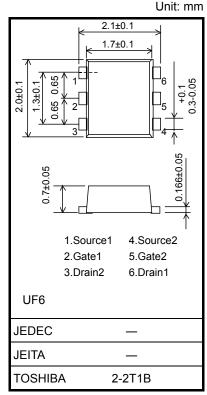
 $R_{on} = 226 \text{ m}\Omega \text{ (max)} (@V_{GS} = -10 \text{ V})$

Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	30	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC	Ι _D	1.6	٨
	Pulse	I _{DP}	3.2	A

Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	-30	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC	I _D	-1.4	А
	Pulse	I _{DP}	-2.8	A



Weight: 7.0 mg (typ.)

Absolute Maximum Ratings (Ta = 25 °C) (Q1, Q2 Common)

Characteristics	Symbol	Rating	Unit
Drain power dissipation	P _D (Note 1)	500	mW
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	–55 to 150	°C

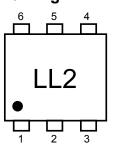
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

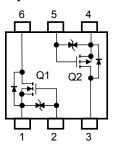
Note1: Mounted on an FR4 board. (total dissipation)

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ mm}, \text{Cu Pad}: 645 \text{ mm}^2)$

Marking



Equivalent Circuit (top view)



Start of commercial production 2008-02

Q1 Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Conditions	Min	Тур.	Мах	Unit
Drain-source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	30	—		V
		V (BR) DSX	$I_D = 1 \text{ mA}, V_{GS} = -20 \text{ V}$	15	—		
Drain cutoff current	t	I _{DSS}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	—	1	μΑ
Gate leakage curre	ent	I _{GSS}	$V_{GS}=\pm 16~V,~V_{DS}=0~V$		_	±1	μΑ
Gate threshold volt	age	V _{th}	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	1.0	_	2.6	V
Forward transfer ad	dmittance	Y _{fs}	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 1 \text{A} \qquad (\text{Note 2})$	1.9	3.7		S
Drain-source ON-resistance		Design	$I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}$ (Note 2)	_	96	122	mΩ
		R _{DS (ON)}	$I_D = 0.5 \text{ A}, V_{GS} = 4 \text{ V}$ (Note 2)		130	182	
Input capacitance		C _{iss}		—	180	_	
Output capacitance		C _{oss}	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	_	34	_	pF
Reverse transfer capacitance		C _{rss}		_	27	_	
Total Gate Charge		Qg		—	5.1	_	
Gate–Source Charge Gate–Drain Charge		Q _{gs}	V _{DS} = 15 V, I _D = 1.6 A, V _{GS} = 10 V		3.9	_	nC
		Q _{gd}		_	1.2	_	
Switching time	Turn-on time	t _{on}	V _{DD} = 15 V, I _D = 0.5 A		9.5	_	
	Turn-off time	t _{off}	V_{GS} = 0 to 4 V, R_{G} = 10 Ω	—	9.0	_	ns
Drain-source forward voltage		V _{DSF}	$I_D = -1.6 \text{ A}, V_{GS} = 0 \text{ V}$ (Note 2)	—	-0.8	-1.2	V

Q2 Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Conditions	Min	Тур.	Max	Unit
Drain-source breakdown voltage		V (BR) DSS	$I_D = -1 \text{ mA}, \text{ V}_{GS} = 0 \text{ V}$	-30	_	_	V
		V (BR) DSX	I _D = -1 mA, V _{GS} = +20 V	-15	_		v
Drain cutoff current		I _{DSS}	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	-10	μA
Gate leakage curre	nt	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	_		±1	μA
Gate threshold volta	age	V _{th}	$V_{DS} = -5 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8	_	-2.0	V
Forward transfer ac	Imittance	Y _{fs}	$V_{DS} = -5 V, I_D = -1 A$ (Note 2)	1.0	2.0		S
Drain-source ON-resistance		D	$I_D = -1.0 \text{ A}, V_{GS} = -10 \text{ V}$ (Note 2)	_	175	226	mΩ
		R _{DS (ON)}	$I_D = -0.5 \text{ A}, V_{GS} = -4.0 \text{ V}$ (Note 2)	_	290	403	
Input capacitance		C _{iss}		_	120		pF
Output capacitance		C _{oss}	V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz	_	32		
Reverse transfer capacitance		C _{rss}		_	21		
Total Gate Charge		Qg		_	2.9		nC
Gate–Source Charge Gate–Drain Charge		Q _{gs}	V _{DS} = -15 V, I _D = -1.4 A, V _{GS} = -10 V	—	2.2	_	
		Q _{gd}		_	0.7		
Switching time	Turn-on time	t _{on}	V _{DD} = -15 V, I _D = -1 A,	_	12	_	
	Turn-off time	t _{off}	V_{GS} = 0 to -4 V, R_{G} = 10 Ω	_	8.5	_	ns
Drain-source forward voltage		V _{DSF}	$I_D = 1.4 \text{ A}, V_{GS} = 0 \text{ V}$ (Note 2)	_	0.87	1.2	V

Note 2: Pulse test

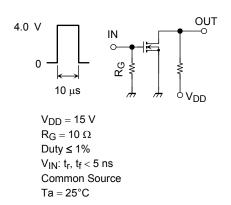
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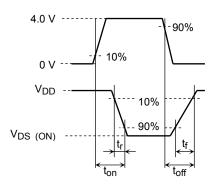
Q1 Switching Time Test Circuit

(a) Test Circuit

(b) V_{IN}

(c) V_{OUT}

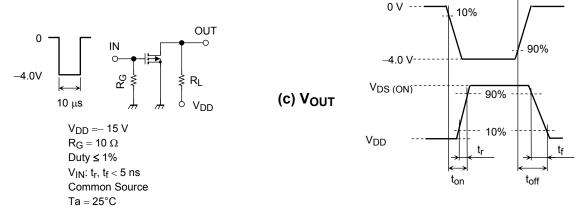




Q2 Switching Time Test Circuit

(a) Test Circuit

(b) V_{IN}



Q1 Usage Considerations

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for the Q1 of the SSM6L40TU). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$.

Take this into consideration when using the device.

Q2 Usage Considerations

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (-1 mA for the Q2 of the SSM6L40TU). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$.

Take this into consideration when using the device.

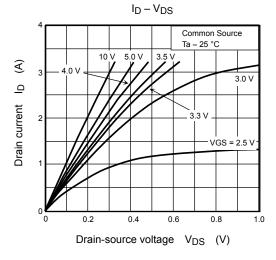
Handling Precaution

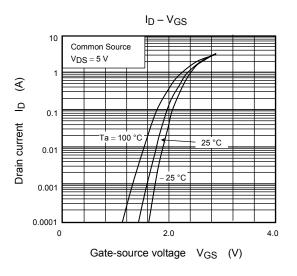
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

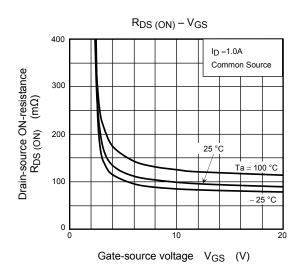
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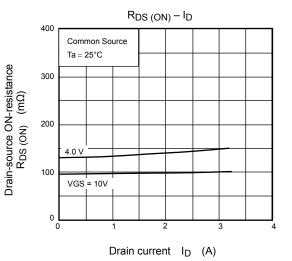
SSM6L40TU

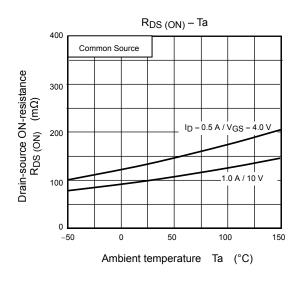
Q1 (N-ch MOSFET)

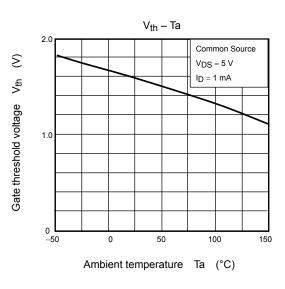






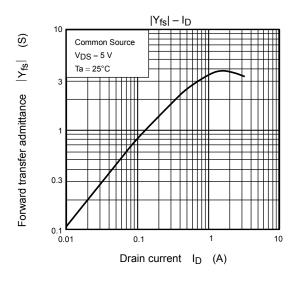


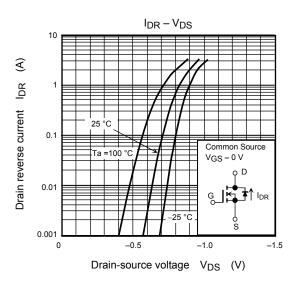


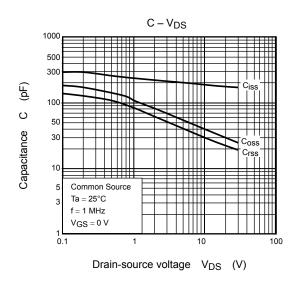


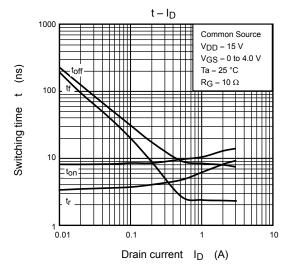
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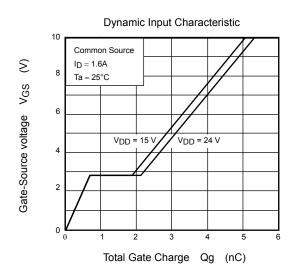
Q1 (N-ch MOSFET)







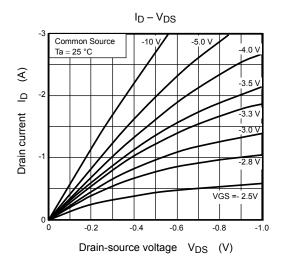


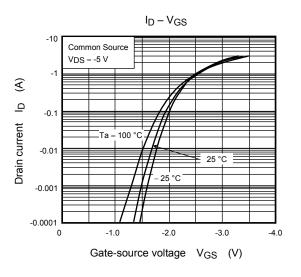


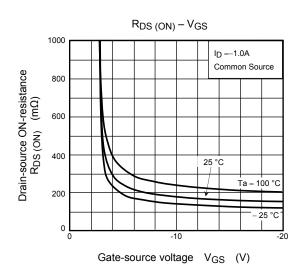
SSM6L40TU

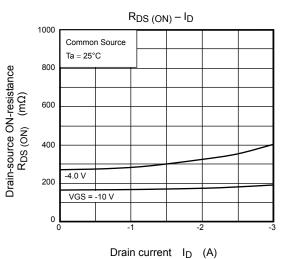
Q2 (P-ch MOSFET)

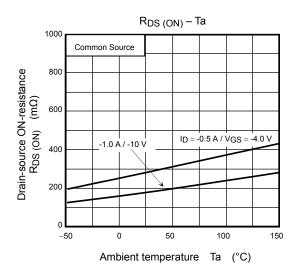
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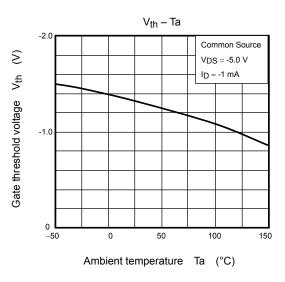




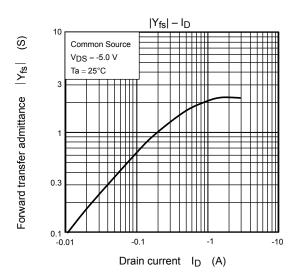


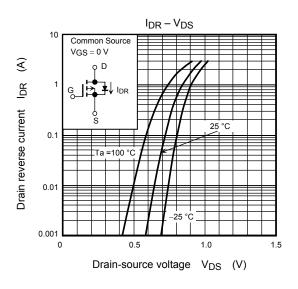


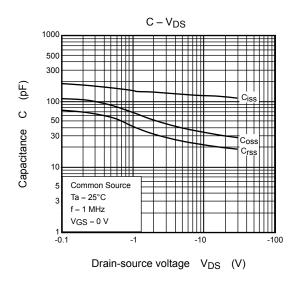


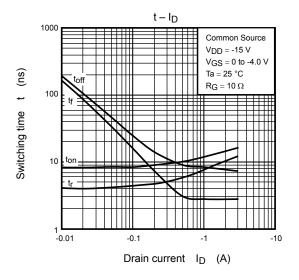


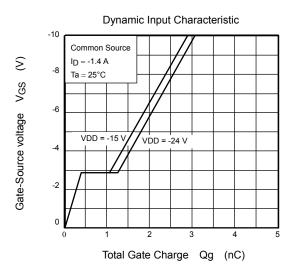
TOSHIBA Q2 (P-ch MOSFET)









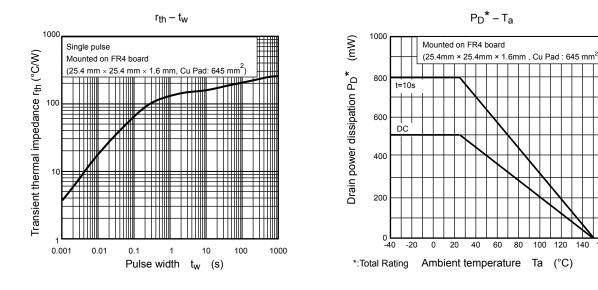


140 160

80 100 120

Q1, Q2 Common

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